

## AMENDMENTS TO THE CLAIMS

Claims 1-169 (Canceled)

170. (currently amended) A ~~chip scale~~ semiconductor component comprising:

a thinned semiconductor die having an outline, a circuit side, a back side, four peripheral edges, and a plurality of die contacts on the circuit side;

a plurality of contact bumps on the die contacts;

a first polymer layer covering the circuit side, the contact bumps and the peripheral edges, the first polymer layer having edge polymer layers of a selected thickness on each the peripheral edges;

a second polymer layer covering the back side, the first polymer layer and the second polymer layer encapsulating the die on six sides such that the component has an a chip scale outline equal corresponding to the outline that of the die plus the selected thickness of the edge polymer layers; and

~~first polymer layer on each peripheral edge; and~~

a plurality of terminal contacts on the contact bumps.

171. (currently amended) The semiconductor component of claim 170 wherein the die is initially contained on a semiconductor wafer and is tested and burned in on the wafer.

~~selected thickness is about 1 mil.~~

172. (currently amended) The semiconductor component of claim 170 wherein the contact bumps comprise metal bumps in a dense area array.

173. (currently amended) The semiconductor component of claim 170 wherein the terminal contacts comprise conductive bumps or balls in a grid array.

174. (currently amended) The semiconductor component of claim 170 wherein the first polymer layer has ~~a first~~ and the contact bumps have a same planar surface.

175. (previously presented) The semiconductor component of claim 170 wherein the second polymer layer has a second planar surface.

176. (previously presented) The semiconductor component of claim 170 further comprising a plurality of conductive vias in the thinned die in electrical communication with the die contacts and with the terminal contacts.

177. (previously presented) The semiconductor component of claim 176 further comprising a plurality of second die contacts on the second polymer layer in electrical communication with the conductive vias.

178. (previously presented) The semiconductor component of claim 170 wherein the second polymer layer comprises a photopolymer.

179. (previously presented) The semiconductor component of claim 170 wherein the second polymer layer comprises a wafer level underfill.

180-261 (canceled)

262. (new) The semiconductor component of claim 170 wherein the backside comprises a planar surface.

263. (new) The semiconductor component of claim 170 wherein the backside comprises a polished surface.

264. (new) The semiconductor component of claim 170 wherein the second polymer layer comprises a tape material.

265. (new) The semiconductor component of claim 170 wherein the first polymer layer on each edge comprises a portion of a polymer filled trench.

266. (new) The semiconductor component of claim 170 wherein the second polymer layer includes at least one pin one indicator.

267. (new) The semiconductor component of claim 170 wherein the first polymer layer includes at least one pin one indicator.

268. (new) The semiconductor component of claim 170 wherein the thinned die comprises a tested and burned in die.

269. (new) The semiconductor component of claim 170 wherein the thinned die is contained on a semiconductor wafer having a polymer support dam proximate to edges thereof.

270. (new) The semiconductor component of claim 170 wherein the first polymer layer comprises a first polymer material and the second polymer layer comprises a second polymer material.

271. (new) The semiconductor component of claim 170 wherein the first polymer layer comprises parylene.

272. (new) The semiconductor component of claim 170 wherein the edge polymer layers form a recess and the second polymer layer is within the recess.